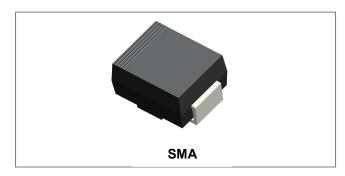


## 10MQ100N-S

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RoHS 🗭

# **10MQ100N-S SCHOTTKY RECTIFIER**



### **Circuit Diagram**



## Features

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Applications**

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

#### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T⊾=105°C, rectangular wave form	1.5	A
DC Current	I <sub>F(DC)</sub>	DC@T∟=120°C	2.1	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	36	А

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 1 A, Pulse, T <sub>J</sub> = 25 °C	0.76	0.78	V
		@ 1.5 A, Pulse, TJ = 25 °C	0.79	0.85	v
	V <sub>F2</sub>	@ 1 A, Pulse, T <sub>J</sub> = 125 °C	0.61	0.63	V
		@ 1.5A, Pulse, T <sub>J</sub> = 125 °C	0.65	0.68	v
Reverse Current*	I <sub>R1</sub>	$@V_R = rated V_R, Pulse,$	0.1	100	uA
		T <sub>J</sub> = 25 °C	0.1	100	uл
	I <sub>R2</sub>	$@V_R = rated V_R, Pulse,$	0.05	1	mA
		T <sub>J</sub> = 125 °C	0.05	1	ШA
Junction Capacitance	CT	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C	36	38	PF
		f <sub>SIG</sub> = 1MHz	30	50	FF
Typical Series Inductance	Ls	Measured lead to lead 5 mm from	2.0		nH
-		package body	2.0	-	
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

\* Pulse width < 300  $\mu$ s, duty cycle < 2%

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# 10MQ100N-S

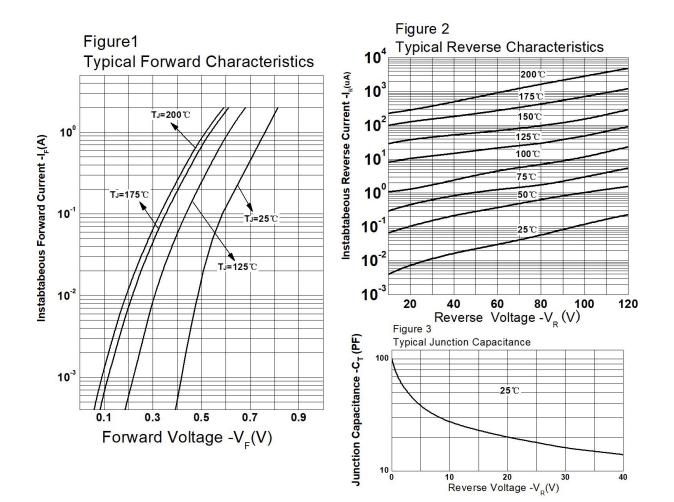
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## Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$	-	80	°C/W
Approximate Weight	wt	-	0.06	g
Case Style	SMA			

### **Ratings and Characteristics Curves**



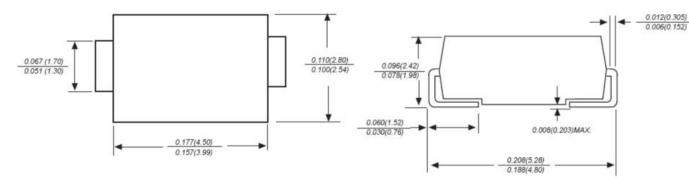


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### Mechanical Dimensions SMA(Millimeters/Inches)

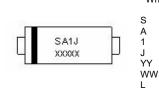


#### **Ordering Information**

Device	Package	Shipping
10MQ100N-S	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

#### **Marking Diagram**

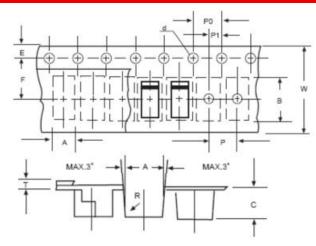


#### Where XXXXX is YYWWL

- = Device Type
- = Package Type
- = Forward Current (1A) = Reverse Voltage (100V)
- = Year
- = Week
- = Lot Number

Cautions: Molding resin Eboxv resin UL:94V-0

### **Carrier Tape & Reel Specification SMA**

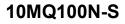


SYMBOL	Millimeters		
STIVIDUL	Min.	Max.	
A	2.97	3.17	
В	5.70	5.90	
С	2.32	2.52	
d	1.40	1.60	
E	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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